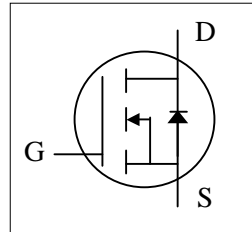




- ▼ Simple Drive Requirement
- ▼ Lower Gate Charge
- ▼ Fast Switching Characteristic
- ▼ Halogen Free & RoHS Compliant Product

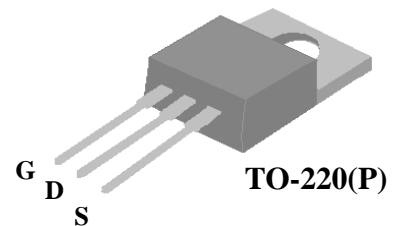


$BV_{DSS}$	100V
$R_{DS(ON)}$	300m $\Omega$
$I_D$	4.4A

### Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is widely preferred for commercial-industrial power applications and suited for low voltage applications such as DC/DC converters.



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	+20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	4.4	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	2.8	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	12	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	12.5	W
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	10	$^\circ\text{C}/\text{W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ\text{C}/\text{W}$



# AP09T10GP-HF

## Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=3A$	-	-	300	$m\Omega$
		$V_{GS}=4.5V, I_D=1.5A$	-	-	600	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=3A$	-	3	-	S
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=80V, V_{GS}=0V$	-	-	25	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge	$I_D=3A$	-	5.5	8.8	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=80V$	-	1.2	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	2.2	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=50V$	-	6.5	-	ns
$t_r$	Rise Time	$I_D=3A$	-	8	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega$	-	10	-	ns
$t_f$	Fall Time	$V_{GS}=10V$	-	3	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	190	300	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	30	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	20	-	pF
$R_g$	Gate Resistance	$f=1.0\text{MHz}$	1	2	4	$\Omega$

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=3A, V_{GS}=0V$	-	-	1.3	V
$t_{rr}$	Reverse Recovery Time	$I_S=3A, V_{GS}=0V,$	-	31	-	ns
$Q_{rr}$	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	47	-	nC

### Notes:

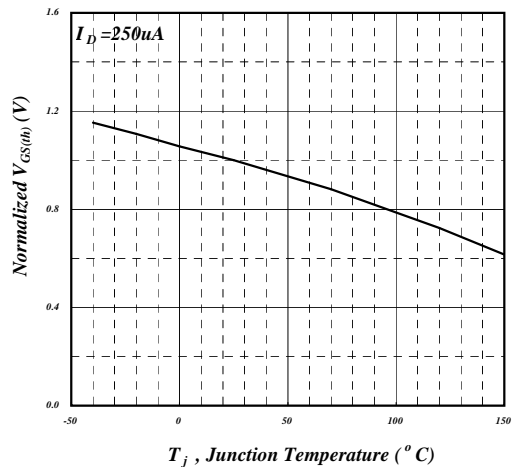
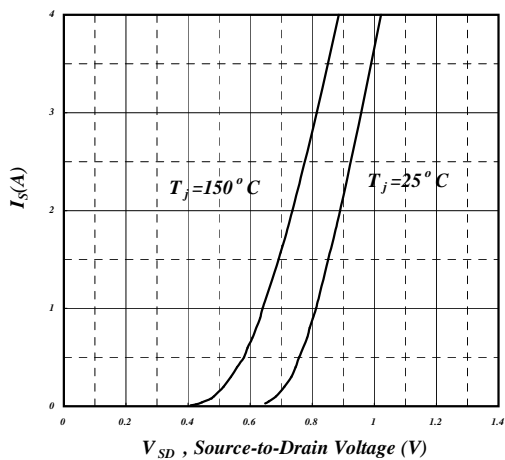
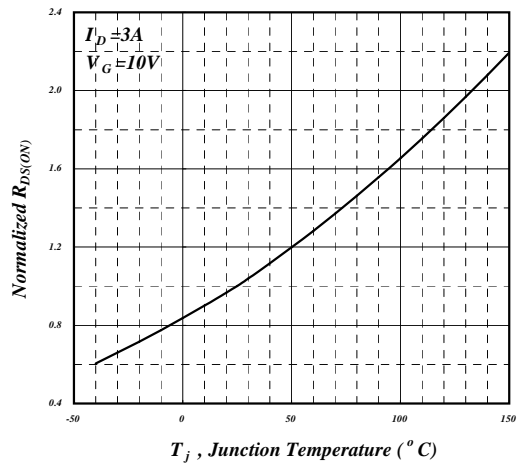
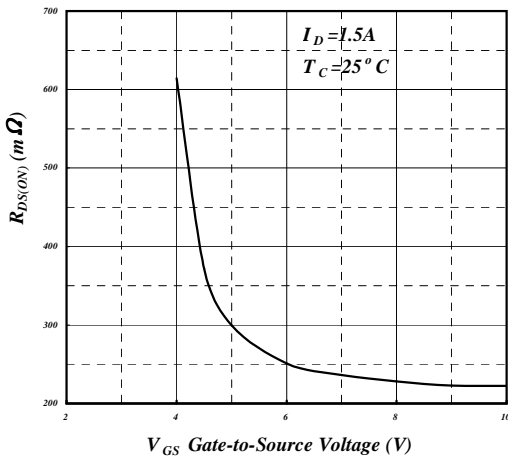
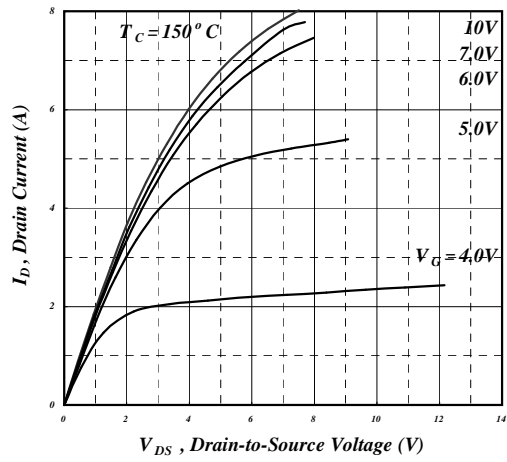
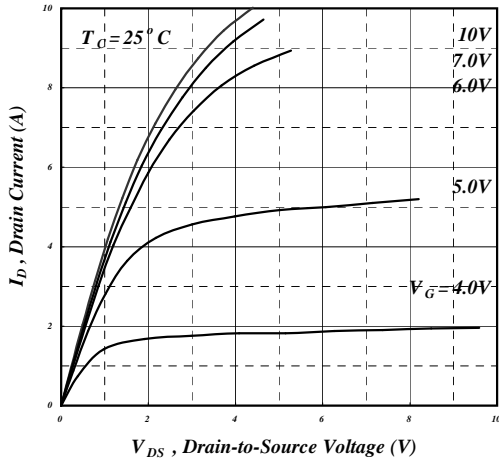
1. Pulse width limited by Max. junction temperature.
2. Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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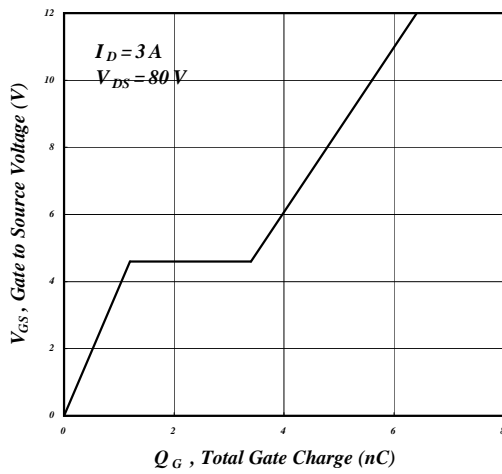


Fig 7. Gate Charge Characteristics

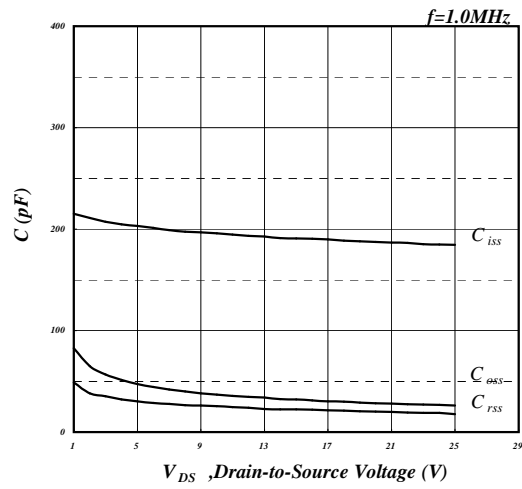


Fig 8. Typical Capacitance Characteristics

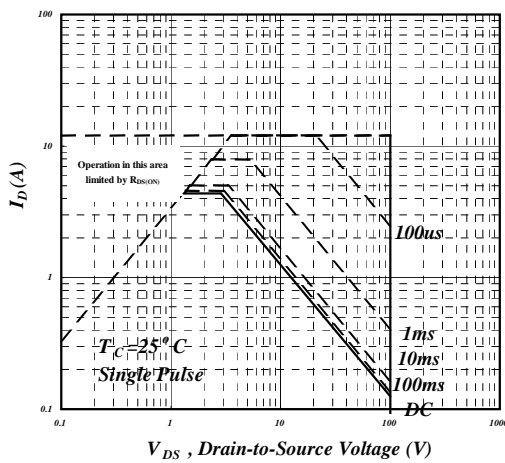


Fig 9. Maximum Safe Operating Area

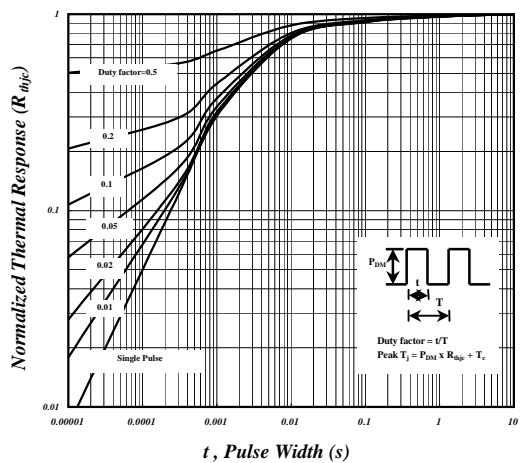


Fig 10. Effective Transient Thermal Impedance

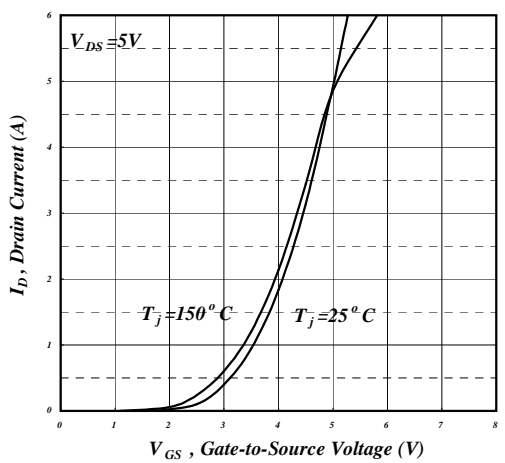


Fig 11. Transfer Characteristics

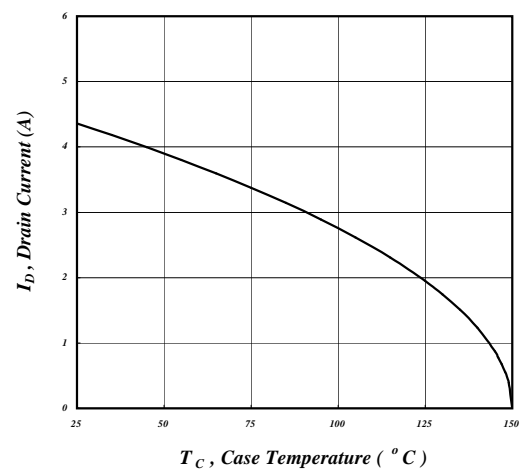


Fig 12. Maximum Continuous Drain Current v.s. Case Temperature